NSD16F3T5G

Switching Diode

The NSD16F3T5G device is a spin-off of our popular SOT-23 three-leaded device. It is designed for switching applications and is housed in the SOT-1123 surface mount package. This device is ideal for low-power surface mount applications where board space is at a premium.

Features

- Reduces Board Space
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V _R	75	Vdc
Forward Current	١ _F	200	mAdc
Peak Forward Surge Current	I _{FM(surge)}	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 1)	290 2.3	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 1)	432	°C/W
Total Device Dissipation, T _A = 25°C Derate above 25°C	P _D (Note 2)	347 2.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	R _{θJA} (Note 2)	360	°C/W
Thermal Resistance, Junction-to-Lead 3	R _{ΨJL} (Note 2)	143	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	–55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

100 mm² 1 oz, copper traces.
 500 mm² 1 oz, copper traces.



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NSD16F3T5G



MARKING DIAGRAM



Т = Device Code

= Date Code Μ

ORDERING INFORMATION

Device	Package	Shipping [†]
NSD16F3T5G	SOT-1123 (Pb-Free)	8000/Tape & Reel

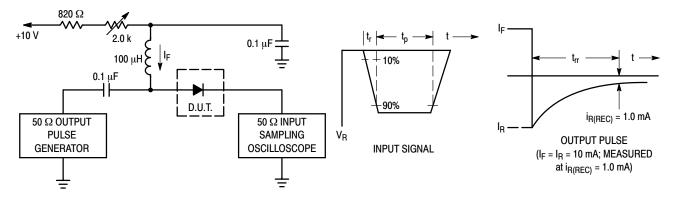
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NSD16F3T5G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Voltage Leakage Current ($V_R = 100 \text{ Vdc}$) ($V_R = 75 \text{ Vdc}, T_J = 150^{\circ}\text{C}$) ($V_R = 25 \text{ Vdc}, T_J = 150^{\circ}\text{C}$)	IR		1.0 50 30	μAdc
Reverse Breakdown Voltage (I _{BR} = 100 μAdc)	V _(BR)	75	-	Vdc
Forward Voltage $(I_F = 1.0 \text{ mAdc})$ $(I_F = 10 \text{ mAdc})$ $(I_F = 50 \text{ mAdc})$ $(I_F = 150 \text{ mAdc})$	V _F	- - -	715 855 1000 1250	mV
Diode Capacitance ($V_R = 0, f = 1.0 \text{ MHz}$)	CD	-	2.0	pF
Forward Recovery Voltage (I _F = 10 mAdc, t _r = 20 ns)	V _{FR}	-	1.75	Vdc
Reverse Recovery Time $(I_F = I_R = 10 \text{ mAdc}, R_L = 50 \Omega)$	t _{rr}	-	6.0	ns
Stored Charge (I _F = 10 mAdc to V _R = 5.0 Vdc, R _L = 500 Ω)	Q _S	-	45	рС

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



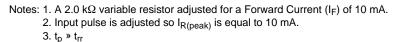


Figure 1. Recovery Time Equivalent Test Circuit

NSD16F3T5G

TYPICAL CHARACTERISTICS

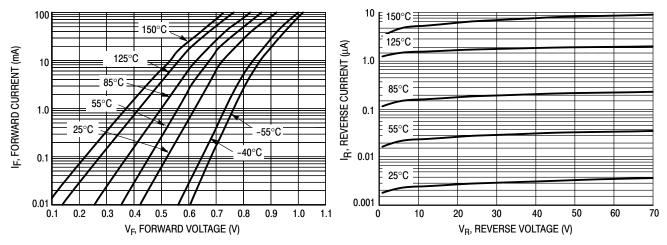
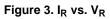


Figure 2. V_F vs. I_F



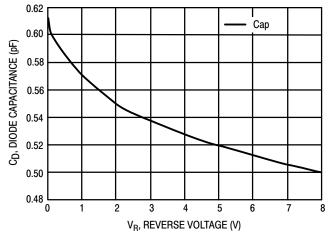


Figure 4. Capacitance

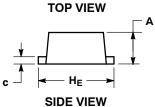




SCALE 8:1



SOT-1123 CASE 524AA ISSUE C





SOLDERING FOOTPRINT*



*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURCE
3. COLLECTOR	3. CATHODE	3. CATHODE	3. ANODE	3. DRAIN

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED	
DESCRIPTION:	SOT-1123, 3-LEAD, 1.0X0	.6X0.37, 0.35P	PAGE 1 OF 1
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DATE 29 NOV 2011

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS.
- CONTROLLING DIMENSION: MILLIMETERS.
 MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE
- MINIMUM THICKNESS OF BASE MATERIAL.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.34	0.40	
b	0.15	0.28	
b1	0.10	0.20	
С	0.07	0.17	
D	0.75	0.85	
Е	0.55	0.65	
е	0.35	0.40	
HE	0.95	1.05	
L	0.185 REF		
L2	0.05	0.15	

GENERIC MARKING DIAGRAM*

X = Specific Device Code M = Date Code

*This information is generic. Please refer to device data sheet for actual part marking.

Pb-Free indicator, "G" or microdot " •", may or may not be present.

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